DISCIPLINE SPECIFIC CORE COURSE – 17: Analog Devices and Circuits (INDSC6B)

CREDIT DISTRIBUTION, ELIGIBILITY AND PRE-REQUISITES OF THE COURSE

Course title & Code	Credits	Credit distribution of the course			Eligibility criteria	Pre-requisite of the course (if any)
		Lecture	Tutorial	Practical/ Practice		
Analog Devices and Circuits (INDSC6B)	04	03	-	01	Class XII passed with Physics + Mathematics/Applied Mathematics + Chemistry/ Computer Science/Informatics Practices	Semiconductor devices

Learning Objectives

The Learning Objectives of this course are as follows:

- To introduce different types of diodes like Tunnel diode, Varactor diode, Schottky diode, Photodiode etc.
- To explain construction and characteristics of JFETs, MOSFETs and UJT
- The student should be able to explain and calculate small signal parameters of MOSFET.
- To learn the basics of MOSFET Circuits.

Learning outcomes

The Learning Outcomes of this course are as follows:

- Explain the operation of Tunnel diode, Varactor diode, Schottky diode, Photodiode etc.
- Reproduce the I-V characteristics of JFET, MOSFET and UJT.
- Analysis of the operation of MOS transistor
- Ability to understand the fundamentals of MOSFET circuits.

SYLLABUS OF DSC-17

UNIT – 1 **(8 hours)**

Special purpose electronic devices: Principal of operation and Characteristics of Tunnel Diode, Varactor Diode, Schottky Diode, Photo diode, Photoconductive cells, IR emitter, Liquid crystal displays, Solar cells, and Thermistor.

UNIT – 2 **(12 hour)**

Junction Field Effect Transistors (JFET): JFET, Construction, Idea of Channel Formation, Pinch-Off and Saturation Voltage, Current-Voltage Output Characteristics. FET Amplifiers: FET Common source Amplifier, Common Drain Amplifier, Generalized FET Amplifier, FET biasing.

UNIT – 3 **(13 hours)**

Metal Oxide Semiconductor Field Effect Transistor (MOSFET): Types of MOSFETs, Circuit symbols, Working and Characteristic curves of Depletion type MOSFET (both N channel and P Channel) and Enhancement type MOSFET (both N channel and P channel). Biasing of MOSFETs, Small Signal Parameters, Common Source amplifier circuit analysis.

UJT, Basic construction and working, Equivalent circuit, intrinsic Standoff Ratio, Characteristics, and Relaxation oscillator

UNIT – 4 **(12 hours)**

MOS Inverter: Introduction, Voltage Transfer Characteristic (VTC), Noise Immunity and Noise margins, Resistive-Load Inverter, CMOS Inverter, DC Characteristics of CMOS Inverter, Calculation of VIL, VIH, VOL, VOH and Vth, Design of CMOS Inverters, Supply Voltage Scaling in CMOS Inverters, Power, and Area considerations

Practical component: **(30 hours)**

1. To verify practically the response of various special purpose electronic devices.
2. To Study the I-V Characteristics of JFET.
3. To Study the I-V Characteristics of MOSFET
4. To obtain the frequency response of a MOSFET amplifier in common source configuration with given specifications.
5. To Study I-V Characteristics of the UJT.
6. NMOS inverter: (a)Transient analysis using Step input and Pulse input. (b) DC analysis (VTC).
7. CMOS inverter: (a)Transient analysis using Step input and Pulse input. (b) DC analysis (VTC).

Essential/recommended readings

1. R. L. Boylestad, L. Nashelsky, K. L. Kishore, Electronic Devices and Circuit Theory, Pearson Education (2006)
2. J. R. C. Jaegar and T. N. Blalock, Microelectronic Circuit Design, Tata McGraw Hill (2010)
3. Donald E. Neaman, “Electronic Circuit, Analysis and Design”, Tata McGraw Hill Publishing Company Limited, Second Edition, 2006.
4. J. Millman and C. C. Halkias, Integrated Electronics, Tata McGraw Hill (2001)
5. CMOS Digital Integrated circuits – Analysis and Design by Sung – Mo Kang, Yusuf Leblebici, TATA McGraw-Hill Pub. Company Ltd.

Suggestive readings

1. D. L. Schilling and C. Belove, Electronic Circuits: Discrete and Integrated, Tata McGraw Hill (2002)
2. Michael Shur, “Physics of Semiconductor Devices,” Prentice Hall
3. Thomas L. Floyd, David M. Buchla, Electronics Fundamentals: Circuits, Devices & Applications, 8th Edition, Pearson education, 2014.

Note: Examination scheme and mode shall be as prescribed by the Examination Branch, University of Delhi, from time to time